

# KM62256C Family

# CMOS SRAM

## 32Kx8 bit Low Power CMOS Static RAM

### FEATURES

- Process Technology : 0.7 $\mu$ m CMOS
- Organization : 32Kx8
- Power Supply Voltage : Single 5V  $\pm$  10%
- Low Data Retention Voltage : 2V(Min)
- Three state output and TTL Compatible
- Package Type : JEDEC Standard  
 28-DIP, 28-SOP, 28-TSOP I-Forward/Reverse

### GENERAL DESCRIPTION

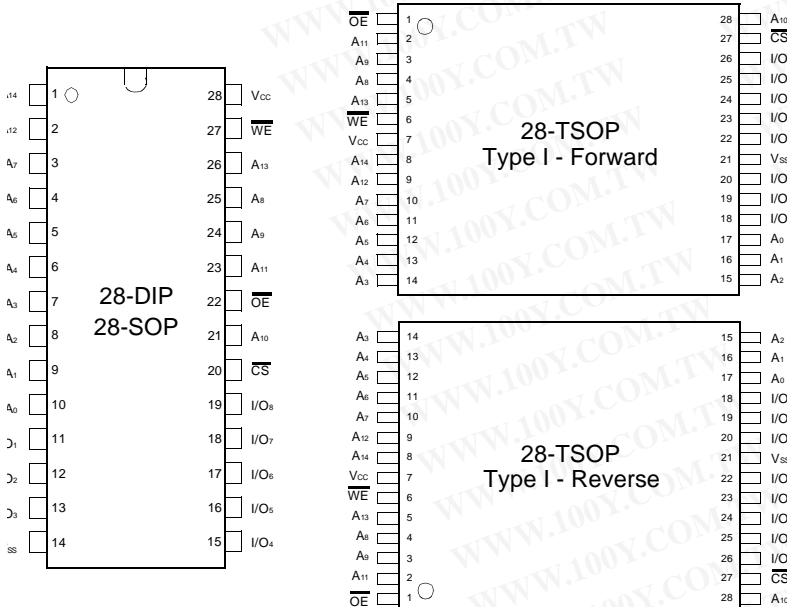
The KM62256C family is fabricated by SAMSUNG's advanced CMOS process technology. The family can support various operating temperature ranges and has various package types for user flexibility of system design. The family also support low data retention voltage for battery back-up operation with low data retention current.

### PRODUCT FAMILY

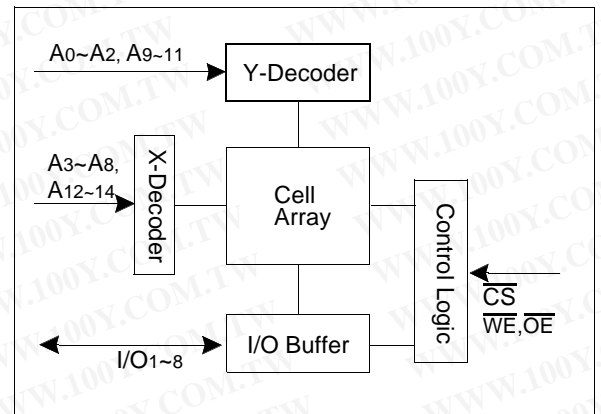
Product Family	Operating Temperature.	Speed (ns)	PKG Type	Power Dissipation	
				Standby (I <sub>SB1</sub> , Max)	Operating (I <sub>CC2</sub> )
KM62256CL KM62256CL-L	Commercial (0~70 $\mu$ C)	45*/55/70ns	28-DIP, 28-SOP 28-TSOP I R/F	100 $\mu$ W 20 $\mu$ W	70mA
KM62256CLE KM62256CLE-L	Extended (-25~85 $\mu$ C)	70/100ns	28-SOP 28-TSOP I R/F	100 $\mu$ W 50 $\mu$ W	
KM62256CLI KM62256CLI-L	Industrial (-40~85 $\mu$ C)	70/100ns	28-SOP 28-TSOP I R/F	100 $\mu$ W 50 $\mu$ W	

\* The parameter is measured with 30pF test load.

### PIN DESCRIPTION



### FUNCTIONAL BLOCK DIAGRAM



Name	Function
A <sub>0</sub> -A <sub>14</sub>	Address Inputs
$\overline{WE}$	Write Enable Input
$\overline{CS}$	Chip Select Input
$\overline{OE}$	Output Enable Input
I/O <sub>1</sub> -I/O <sub>8</sub>	Data Inputs/Outputs
V <sub>cc</sub>	Power(5V)
V <sub>ss</sub>	Ground

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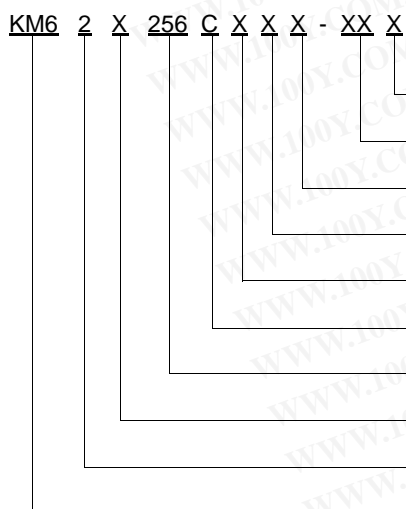
# CMOS SRAM

## PRODUCT LIST & ORDERING INFORMATION

### PRODUCT LIST

Commercial Temp Product (0~70jE)		Extended Temp Products (-25~85jE)		Industrial Temp Products (-40~85jE)	
Part Name	Function	Part Name	Function	Part Name	Function
KM62256CLP-4	28-DIP, 45ns, L-pwr	KM62256CLGE-7	28-SOP, 70ns, L-pwr	KM62256CLGI-7	28-SOP, 70ns, L-pwr
KM62256CLP-4L	28-DIP, 45ns, LL-pwr	KM62256CLGE-7L	28-SOP, 70ns, LL-pwr	KM62256CLGI-7L	28-SOP, 70ns, LL-pwr
KM62256CLP-5	28-DIP, 55ns, L-pwr	KM62256CLGE-10	28-SOP, 100ns, L-pwr	KM62256CLGI-10	28-SOP, 100ns, L-pwr
KM62256CLP-5L	28-DIP, 55ns, LL-pwr	<b>KM62256CLGE-10L</b>	<b>28-SOP, 100ns, LL-pwr</b>	KM62256CLGI-10L	28-SOP, 100ns, LL-pwr
KM62256CLP-7	28-DIP, 70ns, L-pwr	KM62256CLTGE-7	28-TSOP F, 70ns, L-pwr	KM62256CLTGI-7	28-TSOP F, 70ns, L-pwr
KM62256CLP-7L	28-DIP, 70ns, LL-pwr	KM62256CLTGE-7L	28-TSOP F, 70ns, LL-pwr	KM62256CLTGI-7L	28-TSOP F, 70ns, LL-pwr
KM62256CLG-4	28-SOP, 45ns, L-pwr	KM62256CLTGE-10	28-TSOP F, 100ns, L-pwr	KM62256CLTGI-10	28-TSOP F, 100ns, L-pwr
KM62256CLG-4L	28-SOP, 45ns, LL-pwr	KM62256CLTGE-10L	28-TSOP F, 100ns, LL-pwr	KM62256CLTGI-10L	28-TSOP F, 100ns, LL-pwr
KM62256CLG-5	28-SOP, 50ns, L-pwr	KM62256CLRGE-7	28-TSOP R, 70ns, L-pwr	KM62256CLRGI-7	28-TSOP R, 70ns, L-pwr
KM62256CLG-5L	28-SOP, 50ns, LL-pwr	KM62256CLRGE-7L	28-TSOP R, 70ns, LL-pwr	KM62256CLRGI-7L	28-TSOP R, 70ns, LL-pwr
KM62256CLG-7	28-SOP, 70ns, L-pwr	KM62256CLRGE-10	28-TSOP R, 100ns, L-pwr	KM62256CLRGI-10	28-TSOP R, 100ns, L-pwr
KM62256CLG-7L	28-SOP, 70ns, LL-pwr	KM62256CLRGE-10L	28-TSOP R, 100ns, LL-pwr	KM62256CLRGI-10L	28-TSOP R, 100ns, LL-pwr
KM62256CLTG-4	28-TSOP F, 45ns, L-pwr				
KM62256CLTG-4L	28-TSOP F, 45ns, LL-pwr				
KM62256CLTG-5	28-TSOP F, 55ns, L-pwr				
KM62256CLTG-5L	28-TSOP F, 55ns, LL-pwr				
KM62256CLTG-7	28-TSOP F, 70ns, L-pwr				
KM62256CLTG-7L	28-TSOP F, 70ns, LL-pwr				
KM62256CLRG-4	28-TSOP R, 45ns, L-pwr				
KM62256CLRG-4L	28-TSOP R, 45ns, LL-pwr				
KM62256CLRG-5	28-TSOP R, 55ns, L-pwr				
KM62256CLRG-5L	28-TSOP R, 55ns, LL-pwr				
KM62256CLRG-7	28-TSOP R, 70ns, L-pwr				
KM62256CLRG-7L	28-TSOP R, 70ns, LL-pwr				

### ORDERING INFORMATION



- L-Low Low Power, Blank-Low Power or High Power
- Access Time : 4=45ns, 5=55ns, 7=70ns, 10=100ns
- Operating temperature : Blank=Commercial, I=Industrial, E=Extended
- Package Type : G=SOP, P=DIP, TG=TSOP Forward, RG=TSOP Revers
- L-Low Power or Low Low Power, Blank-High Power
- Die Version : C=4th generation
- Density : 256=256K bit
- Blank=5V, V=3.0~3.6V, U=2.7~3.3V
- Organization : 2=x8
- SEC Standard SRAM

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## ABSOLUTE MAXIMUM RATINGS\*

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to Vss	V <sub>IN</sub> ,V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> +0.5	V	-
Voltage on V <sub>CC</sub> supply relative to Vss	V <sub>CC</sub>	-0.5 to 7.0	V	-
Power Dissipation	P <sub>D</sub>	1.0	W	-
Storage temperature	T <sub>STG</sub>	-65 to 150	°C	-
Operating Temperature	T <sub>A</sub>	0 to 70	°C	KM62256CL/L-L
		-25 to 85	°C	KM62256CLE/LE-L
		-40 to 85	°C	KM62256CLI/LI-L
Soldering temperature and time	T <sub>SOLDER</sub>	260°C, 10sec (Lead Only)	-	-

\* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## RECOMMENDED DC OPERATING CONDITIONS\*

Item	Symbol	Min	Typ**	Max	Unit
Supply voltage	V <sub>CC</sub>	4.5	5.0	5.5	V
Ground	V <sub>SS</sub>	0	0	0	V
Input high voltage	V <sub>IH</sub>	2.2	-	V <sub>CC</sub> +0.5V	V
Input low voltage	V <sub>IL</sub>	-0.5***	-	0.8	V

\* 1) Commercial Product : T<sub>A</sub>=0 to 70°C, unless otherwise specified

2) Extended Product : T<sub>A</sub>=-25 to 85°C, unless otherwise specified

3) Industrial Product : T<sub>A</sub>=-40 to 85°C, unless otherwise specified

\*\* T<sub>A</sub>=25°C

\*\*\* V<sub>IL</sub>(min)=-3.0V for t<sub>p</sub> 50ns pulse width

## CAPACITANCE\* (f=1MHz, T<sub>A</sub>=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0V	-	6	pF
Input/Output capacitance	C <sub>IO</sub>	V <sub>IO</sub> =0V	-	8	pF

\* Capacitance is sampled not 100% tested

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## DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions*	Min	Typ**	Max	Unit	
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> =V <sub>SS</sub> to V <sub>CC</sub>	-1	-	1	μA	
Output leakage current	I <sub>LO</sub>	$\overline{CS}=V_{IH}$ or $\overline{WE}=V_{IL}$ V <sub>IO</sub> =V <sub>SS</sub> to V <sub>CC</sub>	-1	-	1	μA	
Operating power supply current	I <sub>CC</sub>	$\overline{CS}=V_{IL}$ , V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> , I <sub>IO</sub> =0mA	-	7	15***	mA	
Average operating current	I <sub>CC1</sub>	Cycle time=1μs 100% duty $\overline{CS}_i \hat{A} 0.2V$ , V <sub>IL</sub> $\hat{A} 0.2V$ V <sub>IN</sub> $\hat{A} V_{CC} - 0.2V$ , I <sub>IO</sub> =0mA	-	-	7****	mA	
	I <sub>CC2</sub>	Min cycle, 100% duty $\overline{CS}=V_{IL}$ , I <sub>IO</sub> =0mA	-	-	70	mA	
Output low voltage	V <sub>OL</sub>	I <sub>OL</sub> =2.1mA	-	-	0.4	V	
Output high voltage	V <sub>OH</sub>	I <sub>OH</sub> =-1.0mA	2.4	-	-	V	
Standby Current(TTL)	I <sub>SB</sub>	$\overline{CS}=V_{IH}$	-	-	1*****	mA	
Standby Current (CMOS)	KM62256CL KM62256CL-L	I <sub>SB1</sub> $\overline{CS}_i \hat{A} V_{CC} - 0.2V$ V <sub>IN</sub> $\hat{A} 0.2V$ or V <sub>IN</sub> $\hat{A} V_{CC} - 0.2V$	L(Low Power)	-	2	100	μA
			LL(L Low Power)	-	1	20	μA
	KM62256CLE KM62256CLE-L		L(Low Power)	-	-	100	μA
		LL(L Low Power)	-	-	50	μA	
	KM62256CLI KM62256CLI-L		L(Low Power)	-	-	100	μA
			LL(L Low Power)	-	-	50	μA

\* 1) Commercial Product : T<sub>A</sub>=0 to 70°C, V<sub>CC</sub>=5V ±10% unless otherwise specified

2) Extended Product : T<sub>A</sub>=-25 to 85°C, V<sub>CC</sub>=5V ±10% unless otherwise specified

3) Industrial Product : T<sub>A</sub>=-40 to 85°C, V<sub>CC</sub>=5V ±10% unless otherwise specified

\*\* T<sub>A</sub>=25°C

\*\*\* 20mA for Extended and Industrial Products

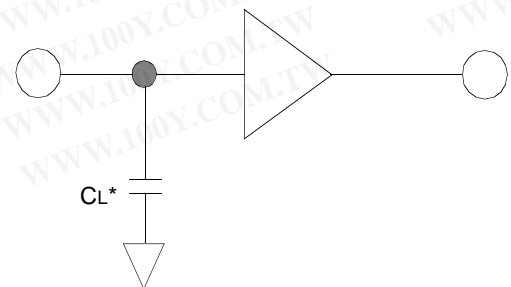
\*\*\*\* 10mA for Extended and Industrial Products

\*\*\*\*\* 2mA for Extended and Industrial Products

## A.C CHARACTERISTICS

### TEST CONDITIONS(1.Test Load and Test Input/Output Reference)\*

Item	Value	Remark
Input pulse level	0.8 to 2.4V	-
Input rising & falling time	5ns	-
input and output reference voltage	1.5V	-
Output load (See right)	C <sub>L</sub> =100pF+1TTL	-
	**C <sub>L</sub> =30pF+1TTL	-



\* Including scope and jig capacitance

\* See DC Operating conditions

\*\* Test load for 45ns commercial products

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## TEST CONDITIONS (2. Temperature and Vcc Conditions)

Product Family	Temperature	Power Supply(Vcc)	Speed Bin	Comments
KM62256CL/L-L	0~70jÉ	5V j¼10%	45*/55/70ns	Commercial
KM62256CLE/LE-L	-25~85jÉ	5V j¼10%	70/100ns	Extended
KM62256CLI/LI-L	-40~85jÉ	5V j¼10%	70/100ns	Industrial

\* The parameter is measured with 30pF test load

## PARAMETER LIST FOR EACH SPEED BIN

Parameter List		Symbol	Speed Bins								Units
			45ns*		55ns		70ns		100ns		
			Min	Max	Min	Max	Min	Max	Min	Max	
Read	Read cycle time	tRC	45	-	55	-	70	-	100	-	ns
	Address access time	tAA	-	45	-	55	-	70	-	100	ns
	Chip select to output	tCO	-	45	-	55	-	70	-	100	ns
	Output enable to valid output	tOE	-	25	-	25	-	35	-	50	ns
	Chip select to low-Z output	tLZ	10	-	10	-	10	-	10	-	ns
	Output enable to low-Z output	tOLZ	5	-	5	-	5	-	5	-	ns
	Chip disable to high-Z output	tHZ	0	20	0	20	0	30	0	35	ns
	Output disable to high-Z output	tOHZ	0	20	0	20	0	30	0	35	ns
	Output hold from address change	tOH	5	-	5	-	5	-	5	-	ns
Write	Write cycle time	tWC	45	-	55	-	70	-	100	-	ns
	Chip select to end of write	tCW	45	-	45	-	60	-	80	-	ns
	Address set-up time	tAS	0	-	0	-	0	-	0	-	ns
	Address valid to end of write	tAW	45	-	45	-	60	-	80	-	ns
	Write pulse width	tWP	40	-	40	-	50	-	60	-	ns
	Write recovery time	tWR	0	-	0	-	0	-	0	-	ns
	Write to output high-Z	tWHZ	0	20	0	20	0	25	0	35	ns
	Data to write time overlap	tDW	25	-	25	-	30	-	50	-	ns
	Data hold from write time	tDH	0	-	0	-	0	-	0	-	ns
	End write to output low-Z	tOW	5	-	5	-	5	-	5	-	ns

\* The parameter is measured with 30pF test load

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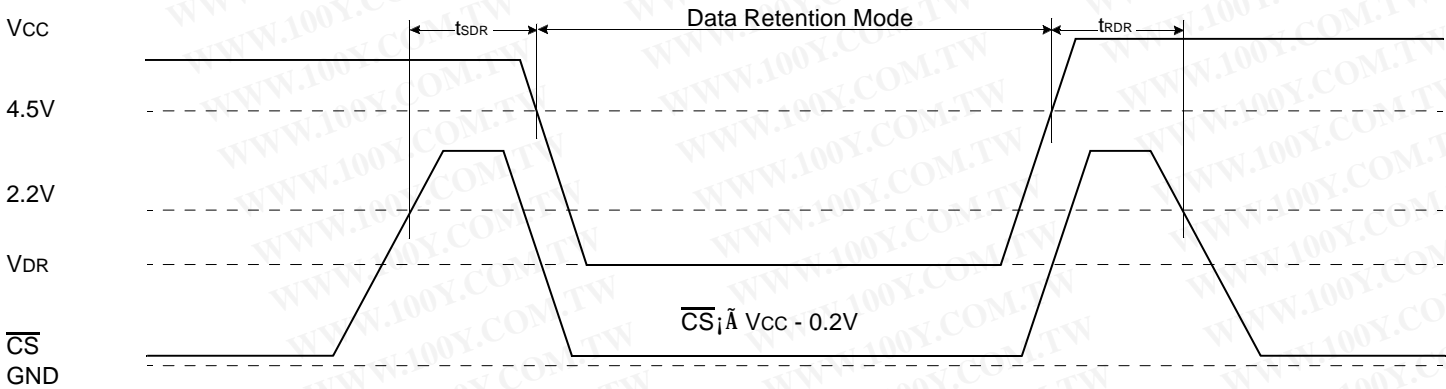
## DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition*	Min	Typ**	Max	Unit
Vcc for data retention	VDR	$\overline{CS}_i \downarrow V_{cc}-0.2V$	2.0	-	5.5	V
Data retention current	IDR	$V_{cc}=3.0V$ $\overline{CS}_i \downarrow V_{cc}-0.2V$	L-Ver	1	50	μA
			LL-Ver	0.5	10	
			L-Ver	-	50	
			LL-Ver	-	25	
			L-Ver	-	50	
			LL-Ver	-	25	
Data retention set-up time	tSDR	See data retention waveform	0	-	-	ms
Recovery time	tRDR		5	-	-	

\* 1) Commercial Product : Ta=0 to 70°C, unless otherwise specified  
 2) Extended Product : Ta=-25 to 85°C, unless otherwise specified  
 3) Industrial Product : Ta=-40 to 85°C, unless otherwise specified  
 \*\* TA=25°C

## DATA RETENTION WAVE FORM

### 1) $\overline{CS}$ Controlled



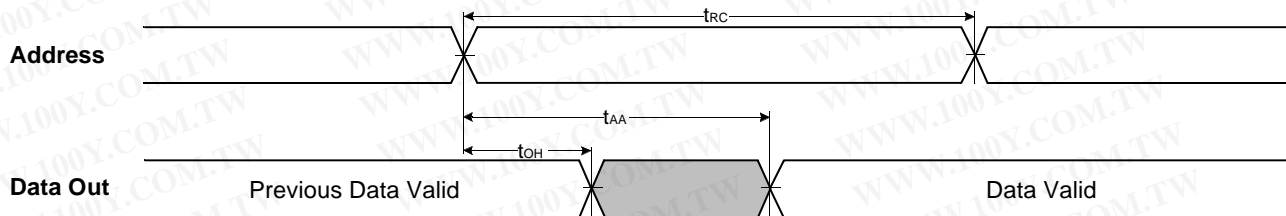
## FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{WE}$	$\overline{OE}$	Mode	I/O Pin	Current Mode
H	X	X	Power Down	High-Z	ISB ISB1
L	H	H	Output Disable	High-Z	Icc
L	H	L	Read	Dout	Icc
L	L	X	Write	Din	Icc

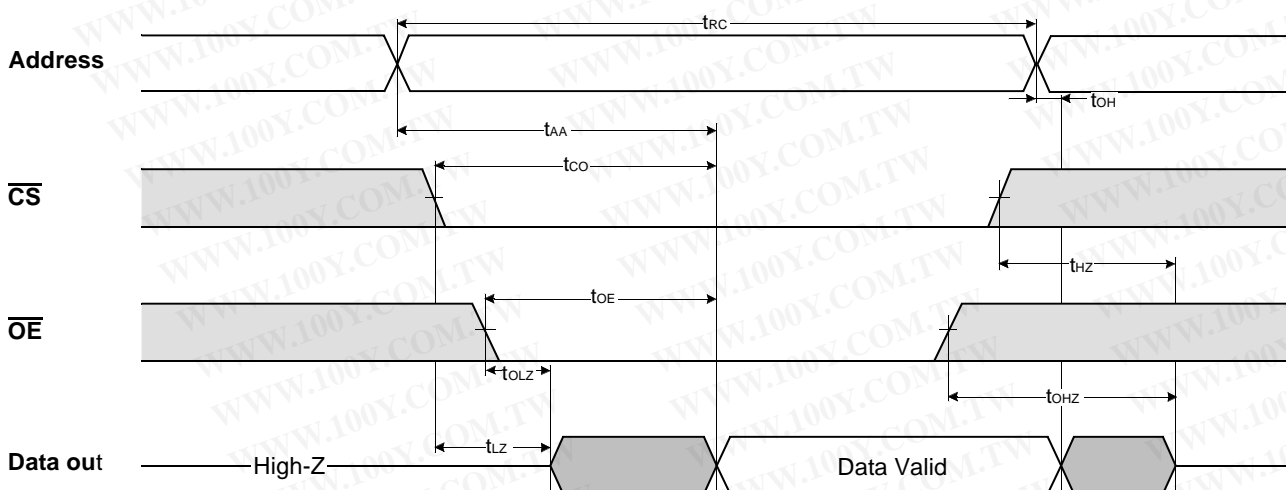
\* X means don't care

**TIMMING DIAGRAMS**

**TIMING WAVEFORM OF READ CYCLE (1) Address Controlled**  
 ( $\overline{CS}=\overline{OE}=V_{IL}$ ,  $\overline{WE}=V_{IH}$ )



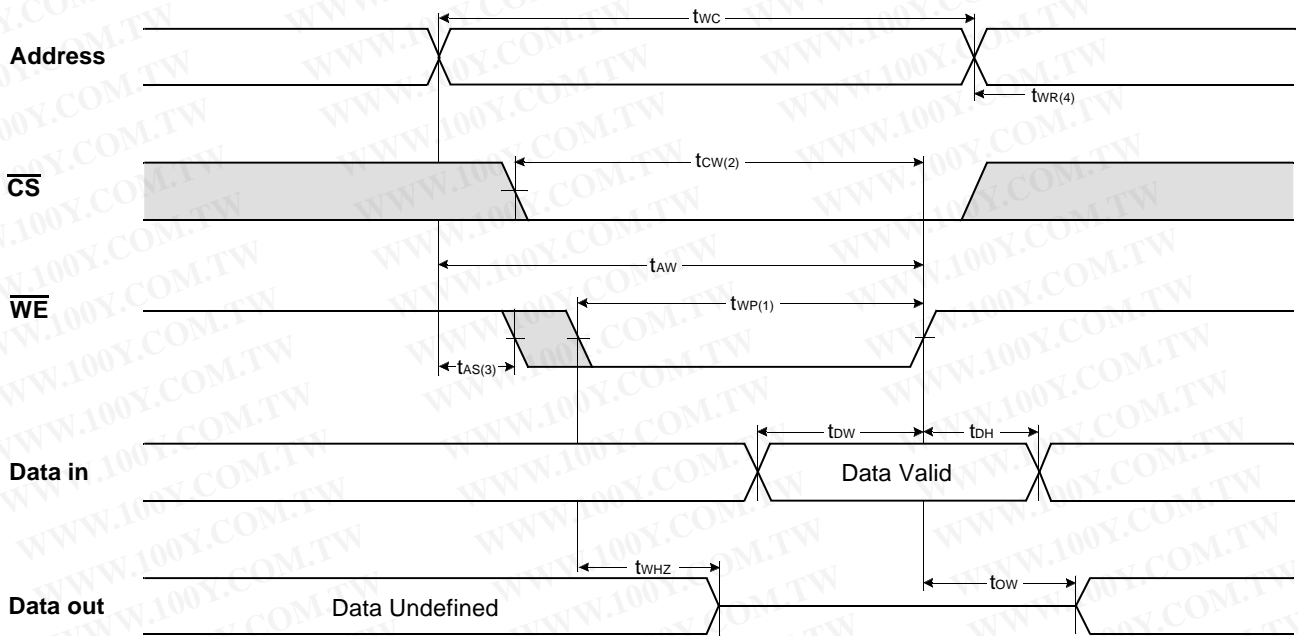
**TIMING WAVEFORM OF READ CYCLE (2)  $\overline{WE}=V_{IH}$**



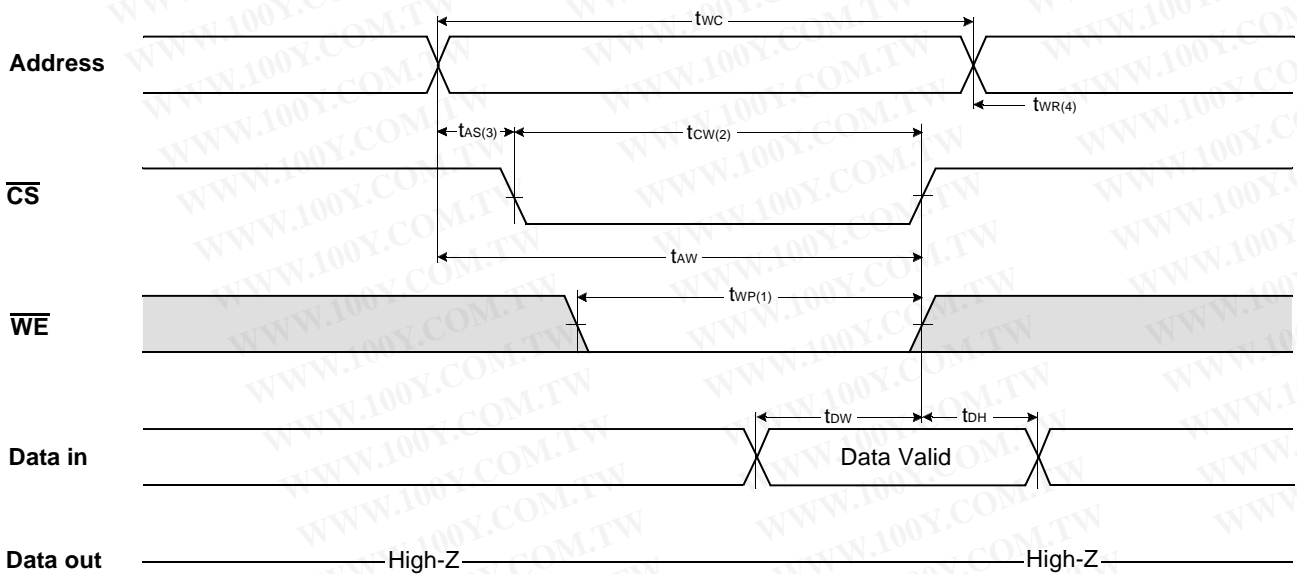
**NOTES (READ CYCLE)**

1. tHZ and tOHZ are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, tHZ(max.) is less than tLZ(min.) both for a given device and from device to device.

**TIMING WAVEFORM OF WRITE CYCLE(1 $\overline{WE}$  Controlled)**



**TIMING WAVEFORM OF WRITE CYCLE(2 $\overline{CS}$  Controlled)**



**NOTES (WRITE CYCLE)**

1. A write occurs during the overlap( $t_{WP}$ ) of low  $\overline{CS}$  and low  $\overline{WE}$ . A write begins at the latest transition among  $\overline{CS}$  going low and  $\overline{WE}$  going low : A write end at the earliest transition among  $\overline{CS}$  going high and  $\overline{WE}$  going high,  $t_{WP}$  is measured from the beginning of write to the end of write.
2.  $t_{CW}$  is measured from the  $\overline{CS}$  going low to end of write.
3.  $t_{AS}$  is measured from the address valid to the beginning of write.
4.  $t_{WR}$  is measured from the end of write to the address change.  $t_{WR}$  applied in case a write ends as  $\overline{CS}$  or  $\overline{WE}$  going high.



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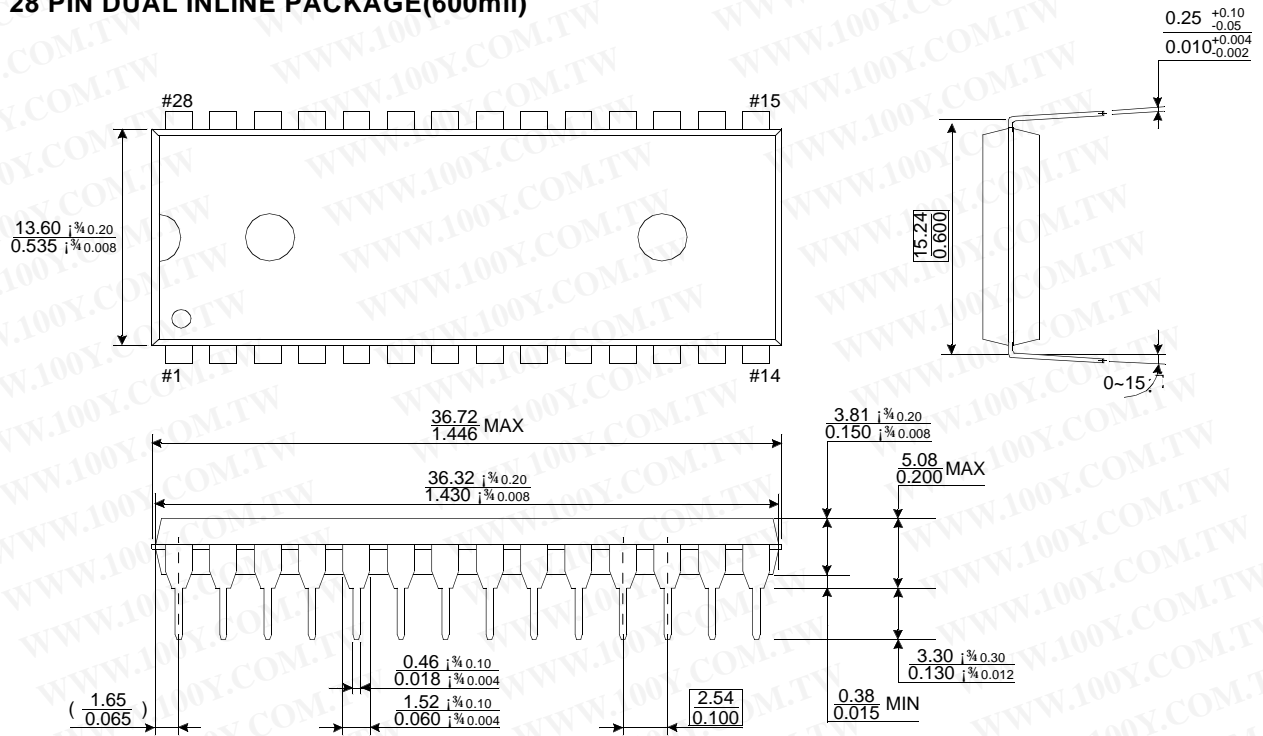
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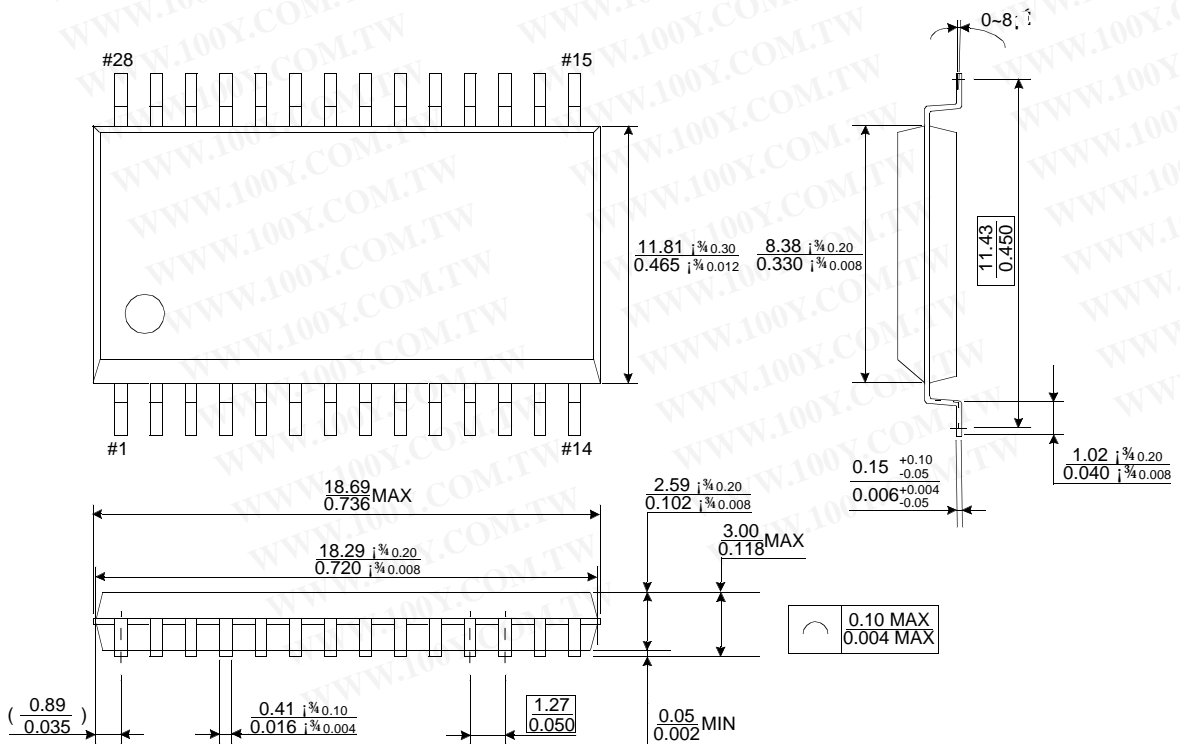
## PACKAGE DIMENSIONS

Units :Millimeters(Inches )

### 28 PIN DUAL INLINE PACKAGE(600mil)



### 28 PIN PLASTIC SMALL OUTLINE PACKAGE(450mil)



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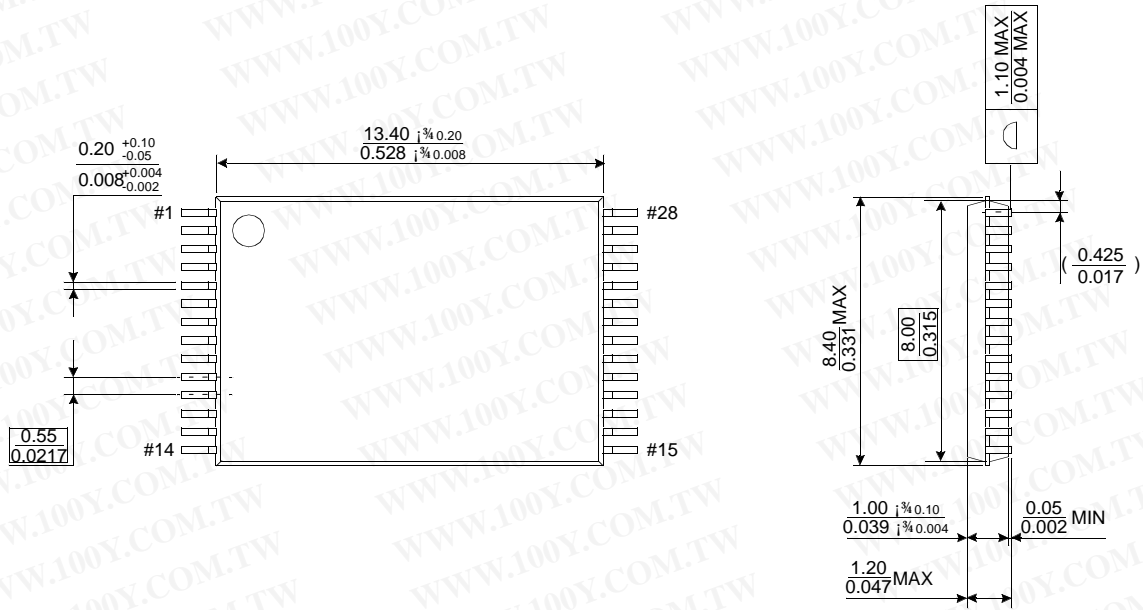
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# CMOS SRAM

## PACKAGE DIMENSIONS

Units :Millimeters(Inches )

### 28 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4F)



### 28 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4R)

